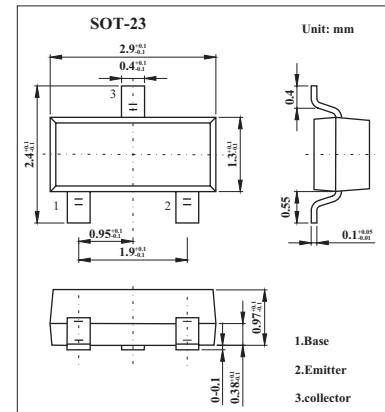


Silicon NPN Epitaxial Planar Type

2SC3547B



■ Features

- Transition frequency is high and dependent on current excellently.

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	20	V
Collector-emitter voltage	V _{CEO}	12	V
Emitter-base voltage	V _{EB0}	3	V
Base current	I _B	15	mA
Collector current	I _C	30	mA
Collector power dissipation	P _C	150	mW
Junction temperature	T _J	125	°C
Storage temperature range	T _{stg}	-55 to +125	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 10 V, I _E = 0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 1 V, I _C = 0			1.0	μA
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1 mA, I _B = 0	12			V
DC current gain	h _{FE}	V _{CE} = 10 V, I _C = 5 mA	70		300	
Transition frequency	f _T	V _{CE} = 10 V, I _C = 10 mA	3	4		GHz
Output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz		1.05	1.35	pF
Collector-base time constant	C _{c.rbb'}	V _{CB} = 10 V, I _C = 5 mA, f = 30 MHz		4.5	9	ps

■ Marking

Marking	HM
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